Reg.					
No					



QPC: RJ23MTECH083

GIET UNIVERSITY, GUNUPUR - 765022

AY 23

M. Tech (First Semester) Examinations, January - 2024

MPCVL1020 - Digital IC Design

(VLSI Design)

Time: 3 hrs Maximum: 70 Marks

(The figures in	the right hand	margin indicate marks.)
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PART – A		$(2 \times 10 = 20 \text{ Marks})$			
Q.1	Answer all questions		CO#	Blooms Level	
a.	What are the components of the data path?		CO1	K1	
b.	What are the characteristics of static CMOS inverter?		CO1	K2	
c.	Which architecture is used to design circuit?		CO1	K2	
d.	What is the dynamic characteristic of MOSFET?		CO2	K1	
e.	What is the basic cell of static RAM?		CO3	K2	
f.	What is a transparent latch?		CO2	K1	
g.	What is the different logic gate used in CMOS?		CO1	K3	
h.	What is the difference between dynamic and static latches?		CO4	K1	
i.	What is the difference between static RAM and dynamic RAM.		CO3	К3	
j.	What are the components of the data path?		CO4	K1	
PART – B Answer ANY FIVE questions					
		(10 x 5	= 50 M	Iarks) Blooms	
				ŕ	
				Blooms	
Answe	Provide detailed explanations for the following circuits:	Marks	CO#	Blooms Level	
Answe	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic	Marks	CO#	Blooms Level K2	
Answe 2. a. b.	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic configurations.	Marks 5	CO# CO1	Blooms Level K2 K3	
Answe 2. a. b.	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic configurations. What are the key considerations in designing the layout of an NMOS inverter, and	Marks 5	CO# CO1	Blooms Level K2 K3	
Answe 2. a. b. 3.a.	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic configurations. What are the key considerations in designing the layout of an NMOS inverter, and how does it differ from the stick diagram?	Marks 5 5 5	CO# CO1 CO2	Blooms Level K2 K3	
Answe 2. a. b. 3.a. b.	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic configurations. What are the key considerations in designing the layout of an NMOS inverter, and how does it differ from the stick diagram? Illustrate the stick diagram and layout of an NMOS inverter.	Marks 5 5 5	CO# CO1 CO2 CO2	Blooms Level K2 K3 K4	
Answe 2. a. b. 3.a. b. 4. a.	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic configurations. What are the key considerations in designing the layout of an NMOS inverter, and how does it differ from the stick diagram? Illustrate the stick diagram and layout of an NMOS inverter. Elaborate on the working principle of an SRAM cell.	Marks 5 5 5 5 5	CO# CO1 CO2 CO2 CO3	Blooms Level K2 K3 K2 K4 K2	
2. a. b. 3.a. b. 4. a. b.	Provide detailed explanations for the following circuits: i) Data path circuit ii) Any one adder circuit. Delve into the intricacies of ratioed circuits and dynamic circuit CMOS logic configurations. What are the key considerations in designing the layout of an NMOS inverter, and how does it differ from the stick diagram? Illustrate the stick diagram and layout of an NMOS inverter. Elaborate on the working principle of an SRAM cell. Write a brief note on the sequencing of dynamic circuits.	Marks 5 5 5 5 5 5	CO# CO1 CO2 CO2 CO3 CO3	Blooms Level K2 K3 K2 K4 K2 K2	

6. a.	Describe the operation and diverse applications of enhancement and depletion			KJ
	mode devices in electronic circuits.			
b.	Explain the concept of accumulation mode in semiconductor devices.	5	CO3	K2
7.a.	Describe the 6-transistor SRAM cell configuration.	5	CO2	K4
b.	Highlight the differences between a latch and a flip-flop.	5	CO2	K2
8. a.	Discuss the applications and challenges associated with sequencing dynamic	5	CO1	К3
	circuits.			
b.	Evaluate the advantages and disadvantages of a latch in electronic circuits.	5	CO2	K2

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